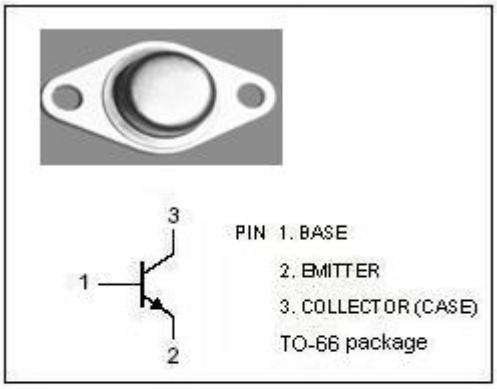
isc Silicon NPN Power Transistor BD162



DESCRIPTION

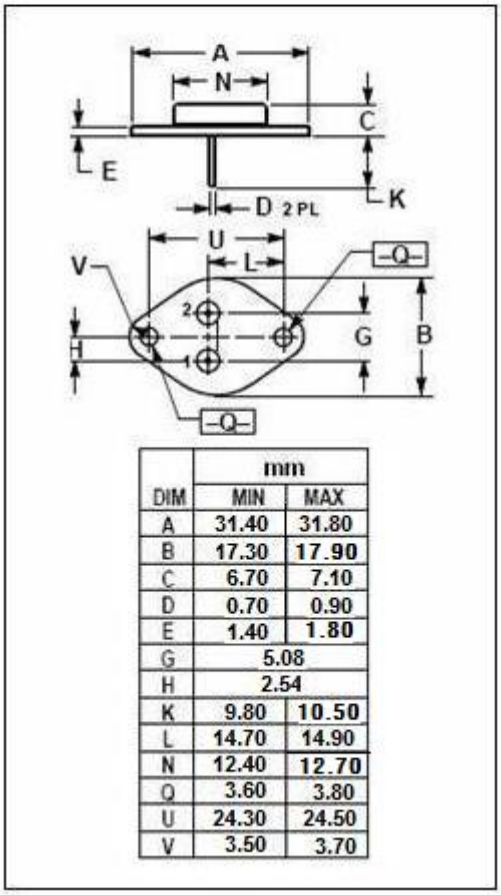
- Continuous Collector Current -I_C= 4A
- Excellent Safe Operating Area
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose switching and amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation@T_C=25℃	15	W
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature	-65~175	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA ; I_B= 0	20		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A		1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		2.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A		2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		3.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V; I_E= 0		100	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0		100	uA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 2V	30	150	
h_{FE-2}	DC Current Gain	I_C= 4A ; V_{CE}= 2V	5		